

PATENT

ATTORNEY DOCKET NO.: 049128-5006



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Commissioner for Patents **BOX PATENT APPLICATION** Washington, D.C. 20231

TRANSMITTAL FOR A NEWLY EXECUTED ORIGINAL APPLICATION UNDER 37 C.F.R. §1.53(b)

This is a request for filing a patent application under 37 C.F.R. §1.53(b) for:

Inventors: Joo Soo LIM and In Byeong KANG

For: LIQUID CRYSTAL DISPLAY DEVICE AND FABRICATING METHOD THEREOF

- This is a new [X] Utility [] Design [] Plant patent application. 1. The papers enclosed to obtain a filing date are as follows: 2. Pages of Specification including 17 _1 Title Page Pages of Claims Page of Abstract Sheets of drawings containing 6 Figures The enclosed drawing(s) are photograph(s), and there is also attached a PETITION TO ACCEPT PHOTOGRAPH(S) AS DRAWING(S) Combined Declaration and Power of Attorney 3.
 - Enclosed and is executed by all Inventors. [X]
 - Not Enclosed. This application is being filed under the provisions of 37 C.F.R. §1.53(f). Applicant(s) await notification from the Patent and Trademark Office of the time set for filing the Declaration and paying the filing fees.

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4.	Langu [X] []				
5.	Assign	nment			
	[X]	An assignment of Form-1595, Reco			CCD CO., LTD and a PTO nclosed.
	[]	An assignment wi	ill be filed at a la	ter date.	
6.	Priority - foreign applications under 35 U.S.C. §119(a)-(d) or §365(b) or PCT international applications under 35 U.S.C. §365(a) designating at least one country other than the U.S. [X] Priority of the following foreign application is claimed:				
		Country	Applica	tion No.	Filed
]	Korea	P00-26876		May 19, 2000
	Certified copy: [X] is attached. [] will follow.				
7.	Priori	ty based on provision	onal application((s) - 35 U.S.C. §	119(e)
	[] Pr	iority of the follow	ing provisional a	pplication(s) is	claimed:
		Application No.			Filed
	Application No.				1 nea

A.	Relate Back -	35	U.S.C.	§119	(e)
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[]	Amend	the specification b	by inserting before the first line the sentence:
	"This a	oplication claims p	priority of copending provisional application(s)
	No	filed on	"

8. Small entity status

[] A statement claiming small entity status under 37 C.F.R. §§1.9 and 1.27 is enclosed.

9. Fee Calculation (37 C.F.R. §1.16)

CLAIMS FOR FEE CALCULATION					
	Number Filed	Number Extra	at Rate of	Basic Fee Utility \$710.00 Design \$320.00	
Total Claims (37 C.F.R. §1.16(c))	20 - 20 =	0	\$ 18.00 each=	\$0.00	
Independent Claims (37 C.F.R. §1.16(b))	6 - 3 =	3	\$ 80.00 each=	\$240.00	
Multiple dependent claim(s), if any (37 C.F.R. §1.16(d)) \$270.00			+		
	\$950.00				
Reduction by 1/2 for filing by a small entity				-\$	
TOTAL FILING FEE =				\$950.00	

10. Fee Payment

[] Not Enclosed. NO FEE IS BEING PAID BY CHECK OR DEPOSIT ACCOUNT AT THIS TIME.

This application is being filed under the provisions of 37 C.F.R. §1.53(f). Applicant(s) await notification from the Patent and Trademark Office of the time set for filing the Declaration and paying the filing fees.

[X] Enclosed.

Two checks in the amounts of \$950.00 and \$40.00 representing the basic filing fee of \$710.00, \$240.00 additional independent claims fee and an assignment recording fee of \$40.00 are enclosed.

- 11. [X] Except for issue fees payable under 37 C.F.R. §1.18, the Commissioner is hereby authorized by this paper to charge any additional fees during the entire pendency of this application including fees due under 37 C.F.R. §§1.16 and 1.17 which may be required, including any required extension of time fees, or credit any overpayment to Deposit Account 50-0310. This paragraph is intended to be a CONSTRUCTIVE PETITION FOR EXTENSION OF TIME in accordance with 37 C.F.R. §1.136(a)(3).
- 12. Additional papers enclosed:
 - [X] Assignment Recordation Cover Sheet
 - [X] Assignment
 - [] Form PTO-1449, __ document included
 - [] Declaration of Biological Deposit
 - [] Submission of "Sequence Listing", computer readable copy and/or amendment pertaining thereto for biotechnology invention containing nucleotide and/or amino acid sequence.

Please accord this application an application number and filing date.

Respectfully submitted,

MORGAN, LEWIS & BOCKIUS LLP

Robert J. Goodell

Reg. No. 41,040

Dated: April 24, 2001

Customer No. 009629 MORGAN, LEWIS & BOCKIUS LLP 1800 M Street, N.W. Washington, D.C. 20036 (202) 467-7000

U.S. PATENT APPLICATION

OF

JOO SOO LIM

FOR

LIQUID CRYSTAL DISPLAY DEVICE AND FABRICATING METHOD THEREOF

[0001] This application claims the benefit of Korean Patent Application No. P00-26876 filed May 19, 2000, which is hereby incorporated by reference.

BACKGROUND OF THE INVENTION

Field of the Invention

[0002] This invention relates to a liquid crystal display, and more particularly to a liquid crystal display device and method of fabricating the same that reduces a reflectivity of an LCD display screen.

Description of the Related Art

[0003] Generally, a liquid crystal display (LCD) of an active matrix driving system uses thin film transistors (TFT's) as switching devices to display images. Since such LCD's can be made smaller than cathode ray tubes, they have been widely used as monitors for personal computers or notebook computers, as well as in office automation equipment, such as copy machines, etc., and in portable equipment, such as a cellular phones and pagers, etc.

[0004] Referring to FIGS. 1 and 2, in the conventional LCD device, a gate line 14 and a data line 13 is formed on a rear substrate 1 crossing each other, and a pixel electrode 10 is formed at the interior thereof. A TFT 12 is formed at an intersection between the gate line 14 and the data line 13.

[0005] The TFT 12 includes a gate electrode 3, a source electrode 6 and a drain electrode 7 to apply a data signal at the data line 13 to the pixel electrode 10 during an application of a scanning pulse to the gate electrode 3. The gate electrode 3 is connected to the gate line 14, while the source electrode 6 is connected to the data line 13. The drain electrode 7 is connected, via a contact hole 9, to the pixel electrode 10, which is deposited with a transparent conductive material such as indium-tin-oxide (ITO). A gate insulating film 4, deposited using an inorganic

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insulating material, is formed on the gate electrode 3 and the gate line 14, and an active layer 20 and an ohmic contact layer 5 are deposited thereon. A passivation layer 8 made from either an inorganic insulating material or an organic insulating material is formed on the TFT 12.

[0006] In the conventional LCD device, a storage capacitor 19 is provided on the gate line 14. The storage capacitor 19 accumulates a driving voltage (charge) of the next scanning line during the previous scanning period, to thereby lower the driving voltage. An upper electrode 15 of the storage capacitor 19 is made from a metal or a metal alloy upon formation of the source electrode 6 and the drain electrode 7, as shown in FIG. 3. The gate line 14 that overlaps the upper electrode 15 serves as a lower electrode of the storage capacitor 19. The upper electrode 15 of the storage capacitor 19 is connected, via a contact hole 16 passing through a passivation layer 8, to the pixel electrode 10.

[0007] A black matrix 11 is provided on a front substrate 2, which is opposed to the rear substrate 1, with a liquid crystal therebetween. The black matrix 11 is positioned at a portion other than an effective display area of a pixel to absorb all wavelengths of light incident thereon. Further, on the front substrate 2 there are provided a common electrode, a color filter and an alignment film (not shown) in addition to the black matrix 11.

[0008] Such an LCD device has a problem in that a large amount of reflective light is generated at the display screen due to a structure of the black matrix 11. More specifically, the black matrix 11 does not overlap with a pixel electrode side portion 17 of the drain electrode 7 and a pixel electrode side portion 18 of the upper electrode 15 of the storage capacitor, as shown in FIG. 1, due to its pattern structure. As a result, as shown in FIGS. 2 and 3, when external light is incident on areas O1 and O2 of the black matrix 11, the upper electrode 15 of the storage capacitor and on the drain electrode 7, it is reflected from the upper electrode 15 and the drain electrode 7, which

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are made of metal. Such a reflected light is incident on a user's eye, and reduces the contrast, thereby reducing quality of a displayed image. For instance, since an aircraft cockpit is exposed to direct sunlight, various LCD panels installed in the cockpit of the aircraft generate a large amount of reflected light. Therefore, the LCD panel in an aircraft may have a deterioration of picture clarity due to the reflected light, sometimes causing pilot error.

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SUMMARY OF THE INVENTION

[0009] Accordingly, it is an object of the present invention to provide a liquid crystal display and a fabricating method thereof that reduce a reflectivity of the display screen.

[0010] In order to achieve these and other objects of the invention, a liquid crystal display device according to one aspect of the invention includes a pixel electrode at a pixel area between a gate line and a data line, a switching device at an intersection between the gate line and the data line, the switching device comprising a light-shielding member overlapping the switching device and extending from an end at the pixel electrode side of a metal thin film provided within the switching device into the pixel area, for blocking light incident on the metal thin film.

[0011] A liquid crystal display device according to another aspect of the present invention includes a pixel electrode at a pixel area between a gate line and a data line, a charging device on the gate line, the charging device including a metal thin film, a light-shielding member overlapping the charging device and extending from an end at the pixel electrode side of a metal thin film into the pixel area, for blocking light incident on the metal thin film.

[0012] A liquid crystal display device according to still another aspect of the present invention includes a pixel electrode at a pixel area between a gate line and a data line, a thin film transistor at an intersection between the gate line and the data line and including a first metal thin film a storage capacitor on the gate line and including a second metal thin film, a black matrix at a

boundary portion between pixel areas, first dummy black matrix connected to the black matrix and extending from an end at the pixel electrode side of the metal thin film into the pixel area, and a second dummy black matrix connected to the black matrix and extending from an end at the pixel electrode side of the second metal thin film into the pixel area.

[0013] A method of fabricating a liquid crystal display device according to still another aspect of the present invention includes the steps of forming a pixel electrode at a pixel area between a gate line and a data line, forming a switching device including a metal thin film at an intersection between the gate line and the data line, and forming a light-shielding member for blocking light incident on the metal thin film to overlap with the switching device, the light-shielding member extending from an end at the pixel electrode side of a metal thin film of the switching device into the pixel area.

[0014] A method of fabricating a liquid crystal display device according to still another aspect of the present invention includes the steps of forming a pixel electrode at a pixel area between a gate line and a data line, forming a charging device including a first metal thin film on the gate line, and forming a light-shielding member for blocking light incident on the metal thin film to overlap the metal thin film, the light-shielding member extending from an end at the pixel electrode side of the first metal thin film into the pixel area.

[0015] A method of fabricating a liquid crystal display device according to still another aspect of the present invention includes the steps of forming a pixel electrode at a pixel area between a gate line and a data line on a rear substrate, forming a thin film transistor including a first metal thin film at an intersection between the gate line and the data line on the rear substrate, forming a storage capacitor including a second metal thin film on the rear substrate and overlapping the gate line, forming a black matrix on a front substrate opposed to the rear

substrate at a boundary portion between pixel areas, forming a first dummy black matrix extending from an end at the pixel electrode side of the first metal thin film into the pixel area on the front substrate, and forming a second dummy black matrix extending from an end at the pixel electrode side of the second metal thin film into the pixel area on the front substrate.

BRIEF DESCRIPTION OF THE DRAWINGS

- [0016] These and other objects of the invention will be apparent from the following detailed description of the embodiment of the present invention with reference to the accompanying drawings.
- [0017] In the drawings:
- [0018] FIG. 1 is a plan view showing a structure of one pixel at a rear substrate of a conventional liquid crystal display device;
- [0019] FIG. 2 is a section view of a thin film transistor taken along the line A-A' of FIG. 1;
- [0020] FIG. 3 is a section view of a thin film transistor taken along the line B-B' of FIG. 1;
- [0021] FIG. 4 is a plan view showing a structure of one pixel at a rear substrate of a liquid crystal display device according to an embodiment of the present invention;
- [0022] FIG. 5 is a section view of a thin film transistor taken along the line C-C' of FIG. 4; and
- [0023] FIG. 6 is a section view of a thin film transistor taken along the line D-D' of FIG. 4.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENT

- [0024] As shown in FIGs. 4 and 5, an LCD device according to an embodiment of the present invention includes a gate line 34 and a data line 33 formed on a rear substrate 21 crossing each other. A pixel electrode 30 is formed at the interior thereof. A TFT 32 is formed at an intersection between the gate line 34 and the data line 33.
- [0025] The TFT 32 includes a gate electrode 23, a source electrode 26 and a drain electrode 27 to apply a data signal at the data line 33 to the pixel electrode 30 during an "on" period of a

scanning pulse to the gate electrode 23. The gate electrode 23 is connected to the gate line 34 while the source electrode 26 is connected to the data line 33. The drain electrode 27 is connected to the pixel electrode 30.

Caption Commission Com

[0026] A process of fabricating such a TFT will be described below. First, a metal thin film is formed by depositing aluminum (Al) or copper (Cu) on the rear substrate 1 using, for example, a sputtering technique. The metal thin film is selectively patterned, to remain only at a desired portion of the rear substrate 21 using photolithography. A wet etching method may be used for the photolithography. The patterned metal thin film is formed into the gate electrode 23 and the gate line 34.

[0027] Subsequently, an insulating material, such as silicon oxide or silicon nitride, is deposited onto the entire substrate by chemical vapor deposition (CVD) to form a gate insulating film 24. The gate insulating film 24 covers the gate electrode 23 and the gate line 14. An active layer 40 and an ohmic contact layer 25 are sequentially deposited onto the gate insulating film 4 by, for example, CVD. The active layer 40 is made of an amorphous silicon or polycrystalline silicon, and is not doped with impurities. The ohmic contact layer 25 is made of amorphous silicon or polycrystalline silicon, and is doped with n-type or p-type impurities at a high concentration. The active layer 40 and the ohmic contact layer 25 are patterned by photolithography, including isotropic etching, to remain only at a portion corresponding to the gate electrode 23. The source electrode 26 and the drain electrode 27 are formed on the ohmic contact layer 25. The source electrode 26 and the drain electrode 27 are formed by depositing a metal such as molybdenum (Mo), titanium (Ti) or tantalum (Ta), etc., or a molybdenum alloy, such as MoW, MoTa or MoNb, etc. on the ohmic contact layer 25 using CVD or sputtering, and then patterning it. Upon patterning of the source electrode 26 and the drain electrode 27, the

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ohmic contact layer 25 on the gate electrode 23 is patterned due to an over-etching, to expose the active layer 40.

[0028] On the TFT 32 that has the structure as described above, an inorganic insulating material such as silicon oxide or silicon nitride, or an organic insulating material such as an acrylic compound, BCB (β-stagged-divinyl-siloxane-benzocyclobutene) or PFCB (perfluorocyclobutane), is deposited. The insulating material deposited on the TFT 32 in this manner becomes a passivation layer 28. A portion of the passivation layer 28 covering the drain electrode 27 is patterned. A contact hole 29 exposing the drain electrode 27 is defined in the patterned passivation layer 28. Subsequently, a transparent conductive material, such as ITO or IZO (indium-zinc-oxide), is deposited on the passivation layer 28 and the contact hole 29. The transparent conductive film contacts the drain electrode 27 through the contact hole 29. The transparent conductive film is patterned to remain only at a pixel area between the gate line 34 and the data line 33, thereby forming the pixel electrode 30.

[0029] The LCD device further includes a storage capacitor 39 formed on the gate line 14. The storage capacitor 39 accumulates a driving voltage (charge) for the next scanning line during the previous scanning period, to thereby lower the required driving voltage. An upper electrode 35 of the storage capacitor 39 is formed by patterning a metal or a metal alloy to overlap the gate line 34 upon formation of the source electrode 26 and the drain electrode 27, as shown in FIG. 6. The gate line 34 overlaps the upper electrode 35 and serves as a lower electrode of the storage capacitor 39. The upper electrode 35 of the storage capacitor 39 is connected, via a contact hole 36 formed by patterning of the passivation layer 30, to the pixel electrode 30.

[0030] A black matrix 31 is provided on a front substrate 22, which is opposed to the rear substrate 21, with a liquid crystal therebetween. The black matrix 31 is positioned at a portion

other than an effective display area of a pixel, that is, at a boundary portion between pixels where the TFT 32, the data line 33, the gate line 34 and the storage capacitor 39 are positioned, so as to prevent a color signal interference between pixels and to shut off a reflected light inputted from the display screen. To this end, the black matrix 31 includes a first shield 31a overlapping the TFT 32, and a second shield 31b overlapping the storage capacitor 39. The first shield 31a extends, by a desired distance C1, from an end at the pixel electrode side of the drain electrode 27 as shown in FIG. 5, to thereby absorb light incident to the metal thin film of the TFT 32, including the drain electrode 27. The second shield 31b extends, by a desired distance C2, from an end at the pixel electrode side of the upper electrode 35, as shown in FIG. 6 to absorb light incident to the metal thin film of the storage capacitor 39, including the upper electrode 35. The black matrix 31 is formed on the front substrate 22 by coating an organic material, such as polyimide, to which a black pigment is added. Furthermore, on the front substrate 22 there is a common electrode, a color filter and an alignment film (not shown), in addition to the black matrix 31.

[0031] As described above, the black matrix formed at a boundary portion between pixels extends into the drain electrode of the TFT and the upper electrode of the storage capacitor. Accordingly, a deterioration of contrast caused by a reflected light incident on the metal thin film can be minimized. Such an LCD device is suitable, for example, for a display panel for aircraft cockpits exposed to direct sunlight.

[0032] Although the present invention has been explained by the embodiments shown in the drawings described above, it should be understood by the ordinary skilled person in the art that the invention is not limited to the embodiments, but rather that various changes or modifications

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thereof are possible without departing from the spirit of the invention. Accordingly, the scope of the invention shall be determined only by the appended claims and their equivalents.

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What is claimed is:

1. A liquid crystal display device comprising:

a pixel electrode at a pixel area between a gate line and a data line;

a switching device at an intersection between the gate line and the data line, the switching device comprising a light-shielding member overlapping the switching device and extending from an end at the pixel electrode side of a metal thin film provided within the switching device into the pixel area, for blocking light incident on the metal thin film.

- 2. The liquid crystal display device of claim 1, wherein the light-shielding member is at a front substrate opposed to a rear substrate, the rear substrate including the switching device and the pixel electrode.
- 3. The liquid crystal display device of claim 2, wherein the light-shielding member is a black matrix.
- 4. The liquid crystal display device of claim 1, wherein the switching device is a thin film transistor at the intersection between the gate line and the data line for driving the pixel electrode; and

wherein the metal thin film of the switching device is a drain electrode connected to the pixel electrode.

5. A liquid crystal display device comprising:

a pixel electrode at a pixel area between a gate line and a data line;

a charging device on the gate line, the charging device comprising:

a metal thin film;

a light-shielding member overlapping the charging device and extending from an end at the pixel electrode side of a metal thin film into the pixel area, for blocking light incident on the metal thin film.

- 6. The liquid crystal display device of claim 5, wherein the light-shielding member is formed at a front substrate opposed to a rear substrate that includes the charging device and the pixel electrode.
- 7. The liquid crystal display device of claim 6, wherein the light-shielding member is a black matrix.
- 8. The liquid crystal display device of claim 5, wherein the charging device is a storage capacitor including:

an upper electrode formed with the gate line; and a dielectric layer between the upper electrode and the gate line, wherein the metal thin film serves as the upper electrode.

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- 9. A liquid crystal display device comprising:
- a pixel electrode at a pixel area between a gate line and a data line;
- a thin film transistor at an intersection between the gate line and the data line and including a first metal thin film;
 - a storage capacitor on the gate line and including a second metal thin film;
 - a black matrix at a boundary portion between pixel areas;
- a first dummy black matrix connected to the black matrix and extending from an end at the pixel electrode side of the metal thin film into the pixel area; and
- a second dummy black matrix connected to the black matrix and extending from an end at the pixel electrode side of the second metal thin film into the pixel area.
- 10. The liquid crystal display device of claim 9, wherein the first metal thin film is a drain electrode connected to the pixel electrode, and wherein the second metal thin film is an upper electrode between the gate line and a dielectric layer.

11. A method of fabricating a liquid crystal display device comprising the steps of: forming a pixel electrode at a pixel area between a gate line and a data line;

forming a switching device including a metal thin film at an intersection between the gate line and the data line; and

forming a light-shielding member for blocking light incident on the metal thin film to overlap with the switching device, the light-shielding member extending from an end at the pixel electrode side of a metal thin film of the switching device into the pixel area.

12. The method of claim 11, wherein the switching device and the pixel electrode are formed on a rear substrate; and

wherein the light-shielding member is formed on a front substrate opposed to the rear substrate, with a liquid crystal layer therebetween.

- 13. The method of claim 12, wherein the light-shielding member is a black matrix.
- 14. The method of claim 12, wherein the switching device is a thin film transistor at the intersection between the gate line and the data line for driving the pixel electrode; and

wherein the metal thin film of the switching device is a drain electrode connected to the pixel electrode.

- 15. A method of fabricating a liquid crystal display device comprising the steps of:
 forming a pixel electrode at a pixel area between a gate line and a data line;
 forming a charging device including a first metal thin film on the gate line; and
 forming a light-shielding member for blocking light incident on the metal thin film to
 overlap the metal thin film, the light-shielding member extending from an end at the pixel
 electrode side of the first metal thin film into the pixel area.
- 16. The method of claim 15, wherein the charging device and the pixel electrode are formed at a rear substrate; and

wherein the light-shielding member is formed at a front substrate opposed to the rear substrate with a liquid crystal layer therebetween.

- 17. The method of claim 16, wherein the light-shielding member is a black matrix.
- 18. The method of claim 15, wherein the first metal thin film is an upper electrode over the gate line and a dielectric layer.

19. A method of fabricating a liquid crystal display device comprising the steps of: forming a pixel electrode at a pixel area between a gate line and a data line on a rear substrate;

forming a thin film transistor including a first metal thin film at an intersection between the gate line and the data line on the rear substrate;

forming a storage capacitor including a second metal thin film on the rear substrate and overlapping the gate line;

forming a black matrix on a front substrate opposed to the rear substrate at a boundary portion between pixel areas;

forming a first dummy black matrix extending from an end at the pixel electrode side of the first metal thin film into the pixel area on the front substrate; and

forming a second dummy black matrix extending from an end at the pixel electrode side of the second metal thin film into the pixel area on the front substrate.

20. The method of claim 19, wherein the metal thin film of the thin film transistor is a drain electrode connected to the pixel electrode; and

wherein the second metal thin film is an upper electrode between the gate line and a dielectric layer.

ABSTRACT

A liquid crystal display device includes a pixel electrode at a pixel area between a gate line and a data line, a switching device at an intersection between the gate line and the data line, the switching device comprising a light-shielding member overlapping the switching device and extending from an end at the pixel electrode side of a metal thin film provided within the switching device into the pixel area, for blocking light incident on the metal thin film.

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FIG.1 CONVENTIONAL ART

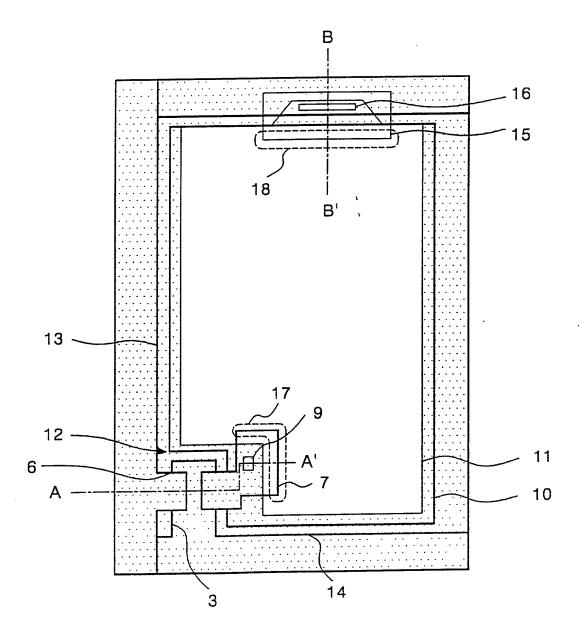


FIG.2 CONVENTIONAL ART

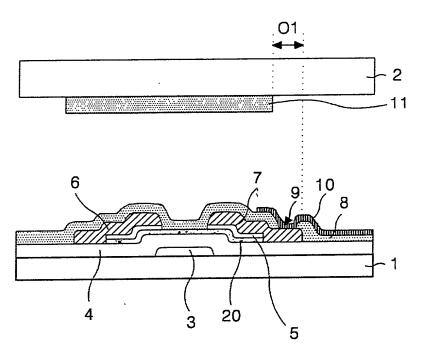


FIG.3 CONVENTIONAL ART

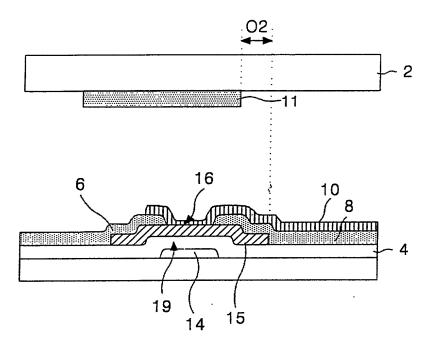


FIG.4

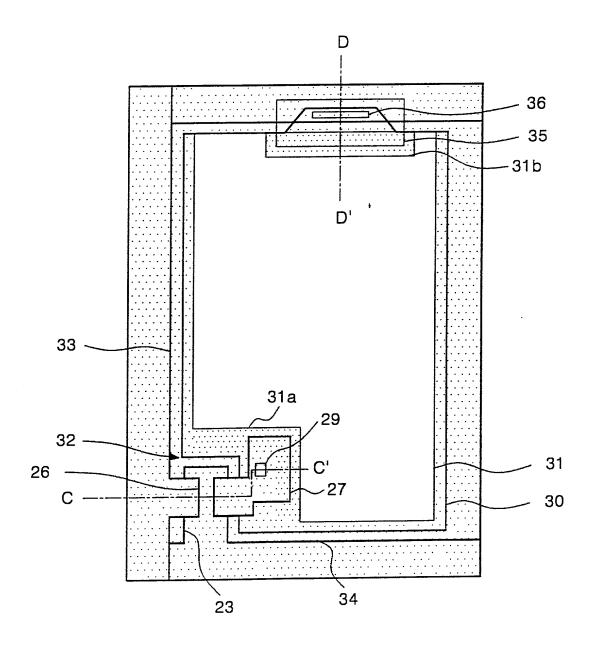


FIG.5

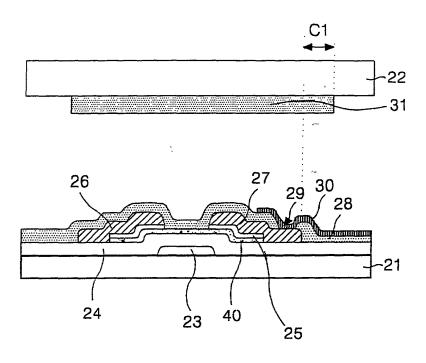
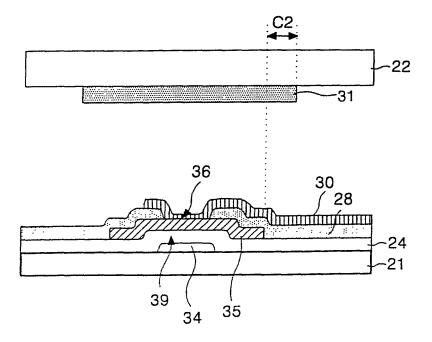


FIG.6



COMBINED DECLARATION FOR PATENT APPLICATION AND POWER OF ATT U.S. DEPARTMENT OF COMMERCE							
	Patent and Trademark Office						
			ATTORNEY D	OCKET NO.: 049128-5006			
	As a below named inventor, I hereby	declare that:					
	My residence, post office address and	d citizenship are as stated below ne	ext to my name,				
	I believe I am the original, first and so names are listed below) of the subject	ole inventor (if only one name is lit matter which is claimed and for v	isted below) or an original, first a which a patent is sought on the in	and joint inventor (if plural nvention entitled:			
	LIQUID CRYST the specification of which:	TAL DISPLAY DEVICE AND F	ABRICATING METHOD TH	EREOF			
	is attached hereto; or						
A the Ways	was filed as United States application	Serial No on and	was amended on(if applicable); or			
of the first first	was filed as PCT international application (if applicable).	ticle 19					
an wan wan	I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims, as amended by any amendment referred to above.						
	I acknowledge the duty to disclose to the U.S. Patent and Trademark Office information which is material to the patentability of claims presented in this application in accordance with Title 37, Code of Federal Regulations Section 1.56.						
	I hereby claim foreign priority benefits under Title 35, United States Code, Section 119(a)-(d) or Section 365(b) of any foreign application(s) for patent or inventor's certificate or Section 365(a) of any PCT international application(s) designating at least one						
	country other than the United States or inventor's certificate or any PCT in	of America listed below and have a nternational application(s) designated	also identified below any foreign ting at least one country other that	applications(s) for patent an the United States of			
	America filed by me on the same subject matter having a filing date before that of the application(s) of which priority is claimed.						
	PRIOR FOREIGN APPLICATION(S COUNTRY	<u>S):</u>	DATE OF FILING				
	(if PCT, indicate PCT)	APPLICATION NUMBER	(day, month, year)	PRIORITY CLAIMED			
	Korea	P00-26876	19 May 2000	[x]Yes []No			
				[]Yes []No			
				[]Yes []No			
				[] Yes [] No			
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I hereby claim the benef application(s) listed belo U.S. PROVISIONAL APPLICA	ow. U.S. PROV	ISIONAL APPLI	Section119(e) of any	OOCKET NO.: 049128-5006 United States provisional
application(s) listed belo	ow. U.S. PROV	ISIONAL APPLI		United States provisional
	U.S. PROV			
U.S. PROVISIONAL APPLICA			CATIONS	
		U.S.	FILING DATE:	
Section 365(c) of any Pobelow and, insofar as the application(s) in the material acknowledge the duty to material to the patentabe Regulations, Section 1.5 national or PCT international or PCT inter	CT international appute subject matter of element provided by the odisclose to the U.S. ility of claims present 66 which became avaitional filing date of the transfer of the	dication(s) designated of the claims of the	ating the United State of this application is a f Title 35, United State mark Office all infor- ation in accordance w e filing date of the pr	United States application(s) or es of America that is/are listed not disclosed in that/those prior tes Code, Section 112, I mation known to me to be with Title 37, Code of Federal for application(s) and the ESIGNATING THE U.S. FOR
BENEFIT: U.S. APPLICATI	IONS	STAT	US (Check One)	100
	S. FILING DATE	PATENTED	PENDING	ABANDONED

POWER OF ATTORNEY: As a named inventor, I hereby appoint the registered practitioners of Morgan, Lewis & Bockius LLP included in the Customer Number provided below to prosecute this application and to transact all business in the Patent and Trademark Office connected therewith, and direct that all correspondence be addressed to that Customer Number.

Customer Number: 009629

Direct Telephone Calls To: (name and telephone number)

Robert J. Gaybrick 202-467-7000

Combined Declaration for Patent Application and Power of Attorney - (Continued) (includes Reference to PCT International Applications) ATTORNEY DOCKET NO.: 049128-5006				
information and belief are be willful false statements and t	ements made herein of my own knowledge are true and the elieved to be true; and further that these statements were rethe like so made are punishable by fine or imprisonment, Code, and that such willful false statements may jeoparduing thereon.	nade with the knowledge that or both, under Section 1001 of		
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Listing of Inventors Continued on attached page(s): [] Yes [x] No